

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

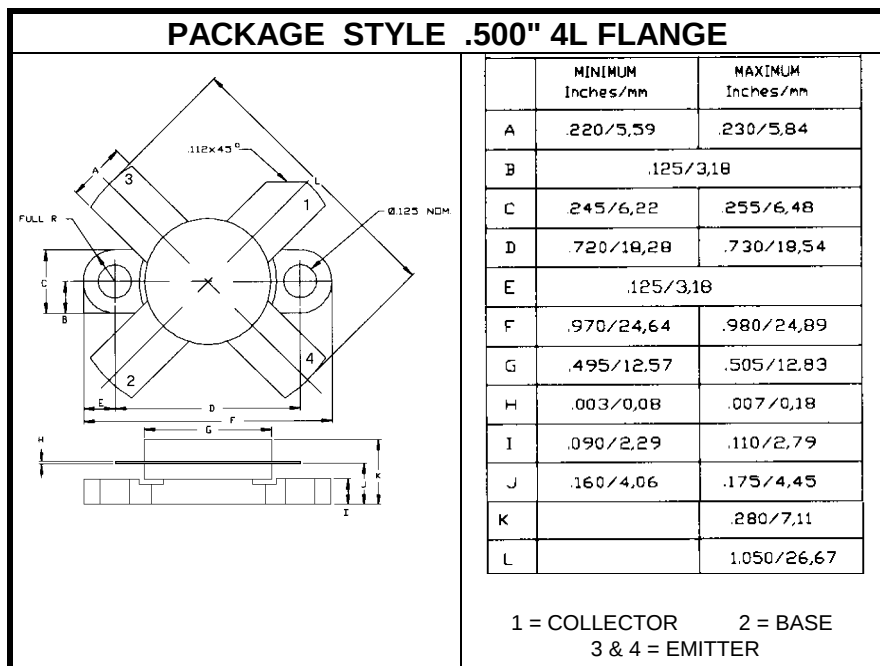
The **ASI MRF460** is Designed for 12.5 Volt Power Amplifier Applications up to 30 MHz.

FEATURES INCLUDE:

- **Omnigold™** Metalization System
- $P_G = 12$ dB Min. @ 30 MHz & 40 W
- Efficiency 40%

MAXIMUM RATINGS

I_C	215 A
V_{CBO}	40 V
V_{CEO}	20 V
V_{EBO}	4.0 V
P_{DISS}	175 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	1.0 $^\circ\text{C/W}$



CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	$I_C = 100$ mA	40			V
BV_{CEO}	$I_C = 100$ mA	20			V
BV_{EBO}	$I_E = 5.0$ mA	4.0			V
I_{CES}	$V_{CE} = 12.5$ V			10	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 1.0$ A	20			---
C_{OB}	$V_{CB} = 12.5$ V $f = 1.0$ MHz		300	350	pF
G_{PE}	$V_{CC} = 12.5$ V $I_C = 4.7$ A $P_{OUT} = 40$ W(PEP)	12	15		dB
IMD	$V_{CC} = 12.5$ V $I_C = 4.7$ A $f = 30$ MHz		-35	-30	dB
η_C		40	45		%